

ABSTRACT:

A method for minimizing the critical dimension growth of a feature on a semiconductor wafer includes performing an etch operation in a reactor 20 and controlling the temperature of the wafer 26 by controlling the pressure of the gas contacting the backside of the wafer 26 and/or providing a heat source 56 such as for example in the chuck 46 or electrode 28 associated with the wafer 26 in order to heat the wafer 26.

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